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Dual N-Channel 30 V (D-S) MOSFET

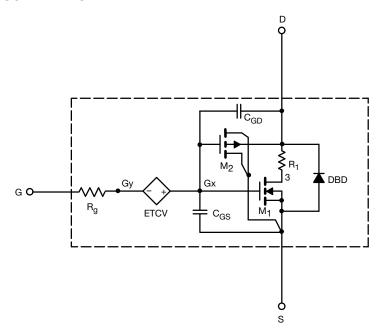
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the N-Channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to +150 °C temperature ranges under the pulsed -12 V to +16 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-channel vertical DMOS
- · Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over the -55 °C to +150 °C temperature range
- · Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer
to the appropriate datasheet of the same number for guaranteed specification limits



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SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.55	1.5	٧
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	0.0026	0.0027	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 7 \text{ A}$	0.0048	0.0044	
		$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}, T_J = 150 ^{\circ}\text{C}$	0.0038	-	
Forward transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 10 \text{ A}$	75	57	S
Dynamic ^b					
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	975	1030	pF
Output capacitance	C _{oss}		356	340	
Reverse transfer capacitance	C _{rss}		30	30	
Total gate charge	Q_g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	14.9	14.8	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	6.9	6.7	
Gate-source charge	Q_{gs}		3.2	3.8	
Gate-drain charge	Q_{gd}		1.6	1.12	
Drain-source body diode characteristics					
Body diode voltage	V_{SD}	I _F = 15 A, V _{GS} = 0 V	0.81	0.85	V

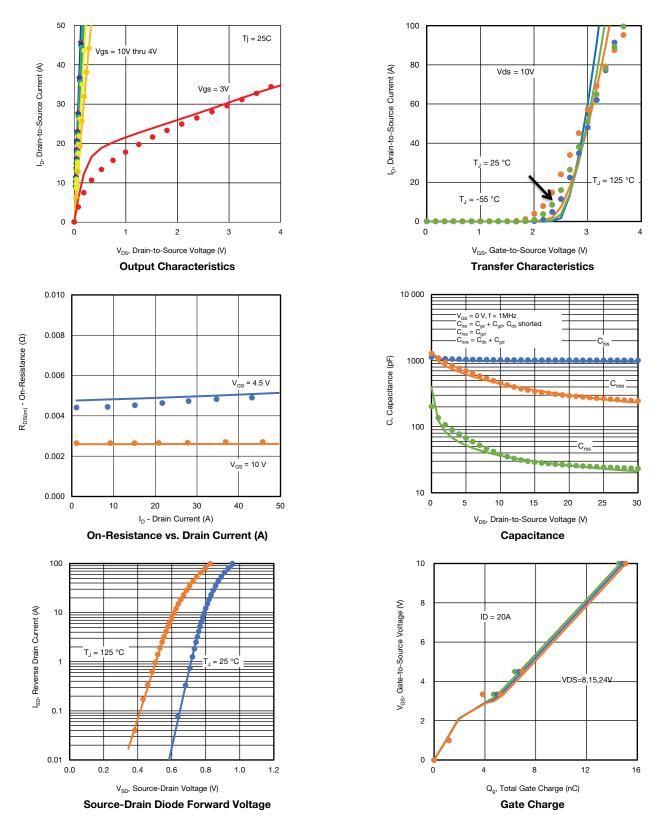
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

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COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25~^{\circ}C$, unless otherwise noted)



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